Abstracts

MESFET Nonlinearities Applied to Predistortion Linearize Design

R.C. Tupynamba and E. Camargo. "MESFET Nonlinearities Applied to Predistortion Linearize Design." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 955-958.

Three different circuit topologies of predistortion linearizes are proposed using MESFETs biased at low drain bias. The design of a C-band linearize using two 1 µm gate length devices is detailed and the achieved results compare favorably with conventional designs which use Schottky diodes. The linearizer reduced by 10 dB the intermodulation products of a 10 W power amplifier operating at 6 GHz and up to 4 dB back-off.

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